# **BUK7M67-60E**

N-channel 60 V, 67 mΩ standard level MOSFET in LFPAK33
19 September 2016 Product data sheet

#### Troduct data cricot

## 1. General description

Standard level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 2. Features and benefits

- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V<sub>GS(th)</sub> rating of greater than 1 V at 175 °C

### 3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- · Ultra high performance power switching

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	60	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	14	Α	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	31	W	
Static characte	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	54	67	mΩ	
Dynamic characteristics								
$Q_{GD}$	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	2.5	-	nC	



#### N-channel 60 V, 67 m $\Omega$ standard level MOSFET in LFPAK33

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simpl	ified outline	Graphic symbol
1	S	Source			D
2	S	Source			
3	S	Source			G T A
4	G	Gate			mbb076 S
mb	D	Mounting base; connected to drain	Li	FPAK33 (SOT1210)	

## 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK7M67-60E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210		

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7M67-60E	76760E

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	60	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	60	V
$V_{GS}$	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C	-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	31	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	14	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	-	10.2	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; Fig. 3	-	58	Α
T <sub>stg</sub>	storage temperature		-55	175	°C

BUK7M67-60E

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Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drain	diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	14	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	58	Α
Avalanche ru	iggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 14 A; $V_{sup}$ ≤ 60 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[1][2]	-	4	mJ

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Refer to application note AN10273 for further information.

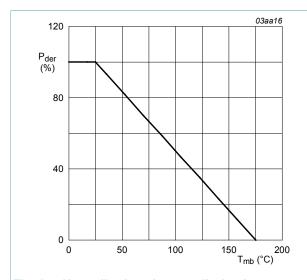


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

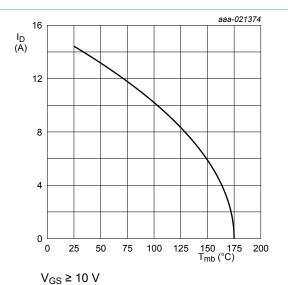


Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 14A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

#### N-channel 60 V, 67 mΩ standard level MOSFET in LFPAK33

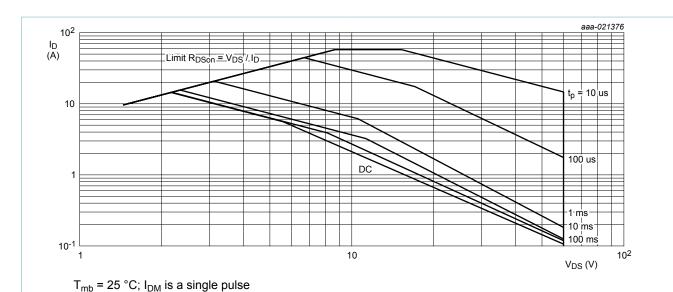
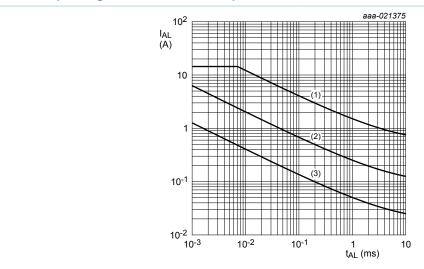


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1)  $T_{j \text{ (init)}}$  = 25 °C; (2)  $T_{j \text{ (init)}}$  = 150 °C; (3) Repetitive Avalanche

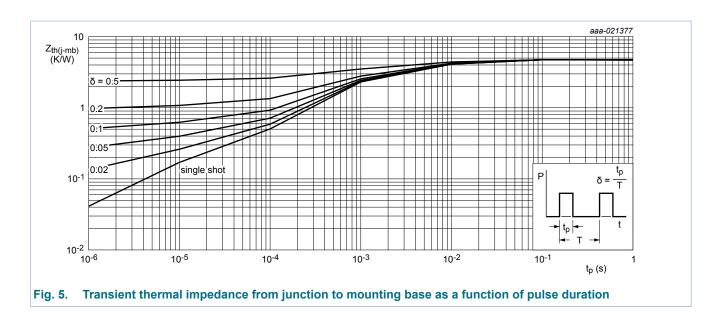
Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

#### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	4.27	4.8	K/W

#### N-channel 60 V, 67 m $\Omega$ standard level MOSFET in LFPAK33



### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS} \\$	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1	-	-	V	
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.01	1	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$	-	54	67	mΩ
resistance	$V_{GS}$ = 10 V; $I_D$ = 5 A; $T_j$ = 175 °C; Fig. 12	-	-	150	mΩ	
Dynamic ch	naracteristics		1			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V;	-	6.7	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	1.6	-	nC
$Q_{GD}$	gate-drain charge		-	2.5	-	nC

BUK7M67-60E

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
C <sub>iss</sub>	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	251	334	pF		
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	48	57	pF		
C <sub>rss</sub>	reverse transfer capacitance		-	36	49	pF		
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 45 V; $R_{L}$ = 5 $\Omega$ ; $V_{GS}$ = 10 V; $R_{G(ext)}$ = 5 $\Omega$ ; $T_{j}$ = 25 °C	-	3.6	-	ns		
t <sub>r</sub>	rise time		-	3.5	-	ns		
t <sub>d(off)</sub>	turn-off delay time		-	6.6	-	ns		
t <sub>f</sub>	fall time		-	3.3	-	ns		
Source-dra	Source-drain diode							
$V_{SD}$	source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$	-	0.87	1.2	V		
t <sub>rr</sub>	reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	16.1	-	ns		
Q <sub>r</sub>	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	10.2	-	nC		

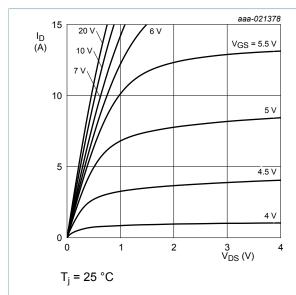


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

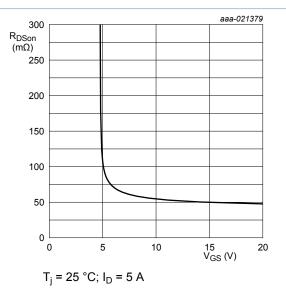


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

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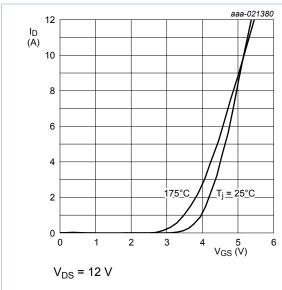


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

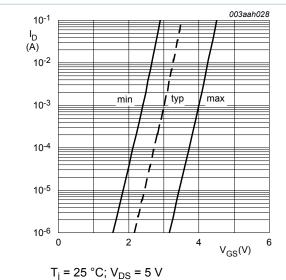


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

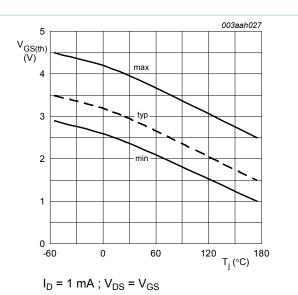


Fig. 9. Gate-source threshold voltage as a function of junction temperature

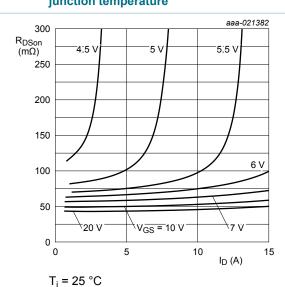


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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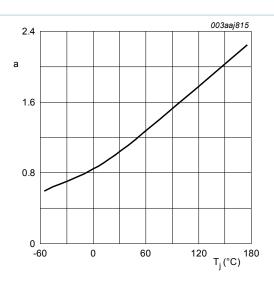


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

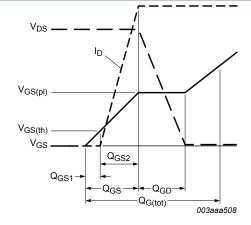
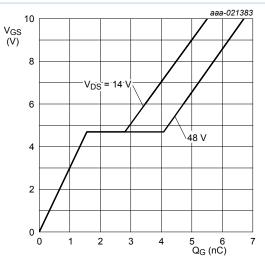
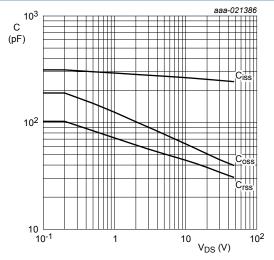


Fig. 14. Gate charge waveform definitions



 $T_j$  = 25 °C;  $I_D$  = 5 A

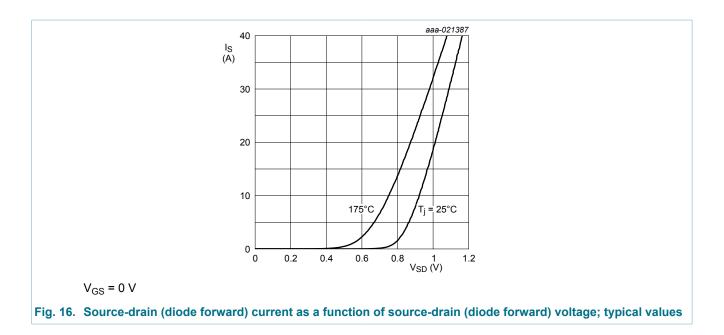
Fig. 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V; f = 1 MHz$ 

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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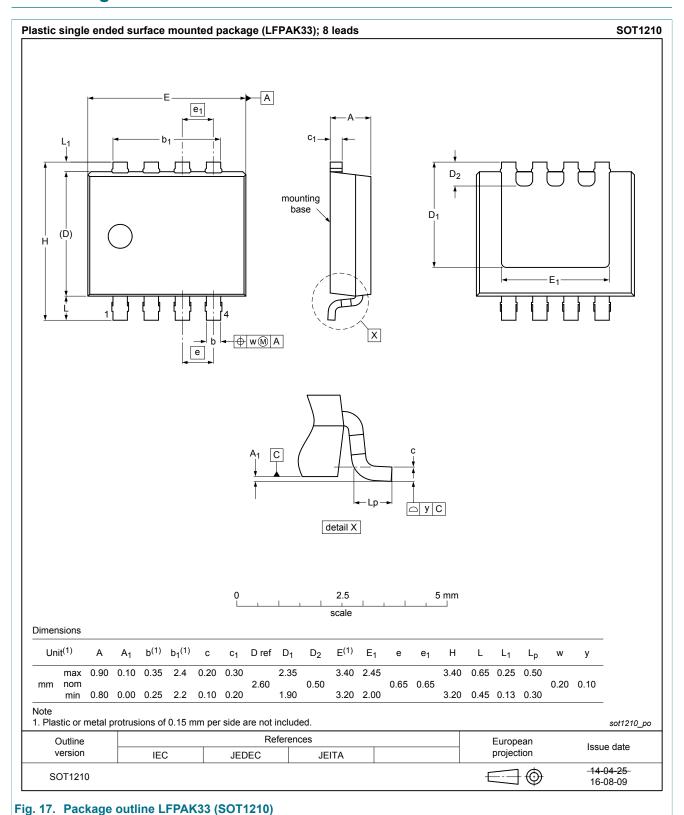


## 11. Application information

For guidance on how to use and understand this datasheet, please refer to application note <a href="Months:AN11158">AN11158</a> "Understanding power MOSFET datasheet parameters".

#### N-channel 60 V, 67 mΩ standard level MOSFET in LFPAK33

## 12. Package outline



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BUK7M67-60E

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#### N-channel 60 V, 67 mΩ standard level MOSFET in LFPAK33

### 13. Legal information

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Document status [1][2]	Product status [3]	Definition
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#### N-channel 60 V, 67 m $\Omega$ standard level MOSFET in LFPAK33

#### 14. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	
9	Thermal characteristics	4
10	Characteristics	5
11	Application information	9
12	Package outline	10
13	Legal information	11
13.1	Data sheet status	11
13.2	Definitions	11
13.3	Disclaimers	11
13.4	Trademarks	12

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